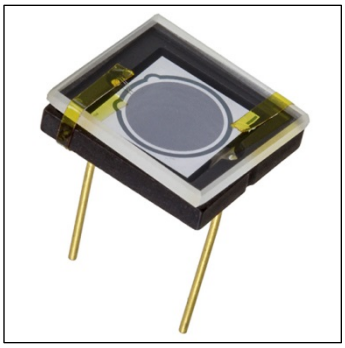
Photodiode Φ5 mm

AXUV20HS1



FEATURES

- Circular Active Area
- Ideal for EUV Detection
- 100% Internal Quantum Efficiency
- High Speed
- Grid Lines 5 Microns, Pitch 100 Microns
- Protective Cover Plate[3]

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ5.01 mm		20		mm^2
Responsivity	(see graph on next page)				A/W
Reverse Breakdown Voltage, V_R	I_R = 1 µA	160			Volts
Capacitance, C	V_R = 0 V		200	800	pF
Rise Time	R_L = 50 Ω, V_R = 150 V			3.5	nsec
Dark Current	V_R = 150 V			100	nA

Thermal Parameters

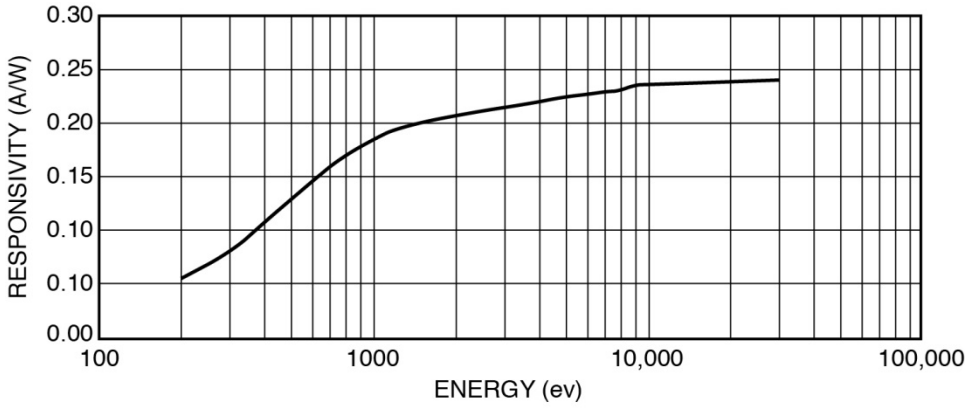
Storage and Operating Temperature Range	
Ambient[1]	-10 ° to 40 °C
Nitrogen or Vacuum	-20 °C to 80 °C
Lead Soldering Temperature[2]	260 °C

[1] Temperatures exceeding these parameters may create oxide growth on the active area.
Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

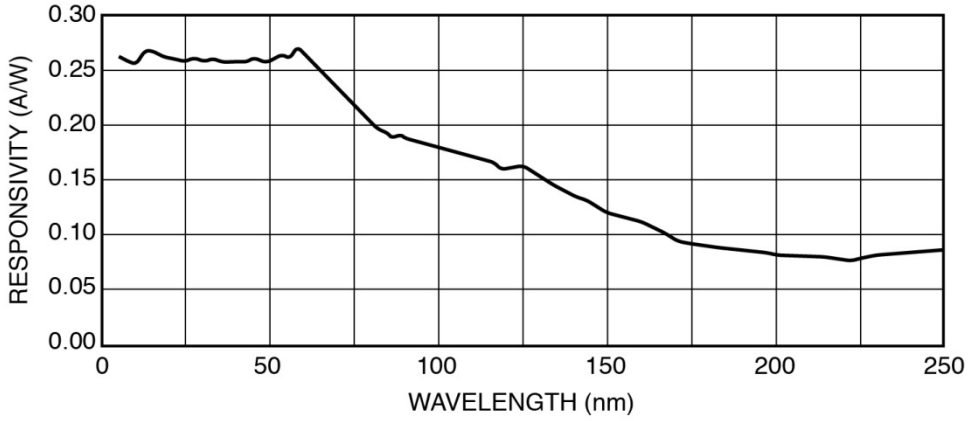
[2] 0.080" from case for 10 seconds.

[3] Shipped with temporary cover to protect the photodiode and wire bonds.
Review the Application Note, “Handling Precautions for AXUV, SXUV, and UVG Detectors”, prior to removing cover.

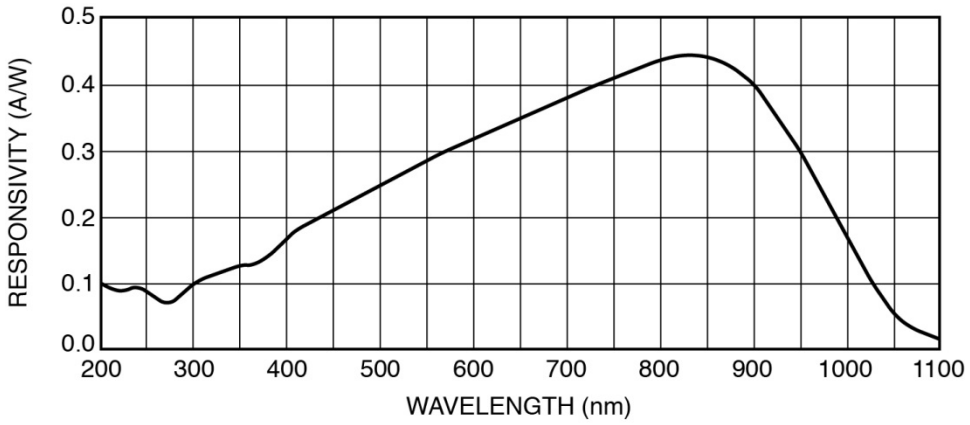
Typical Electron Response



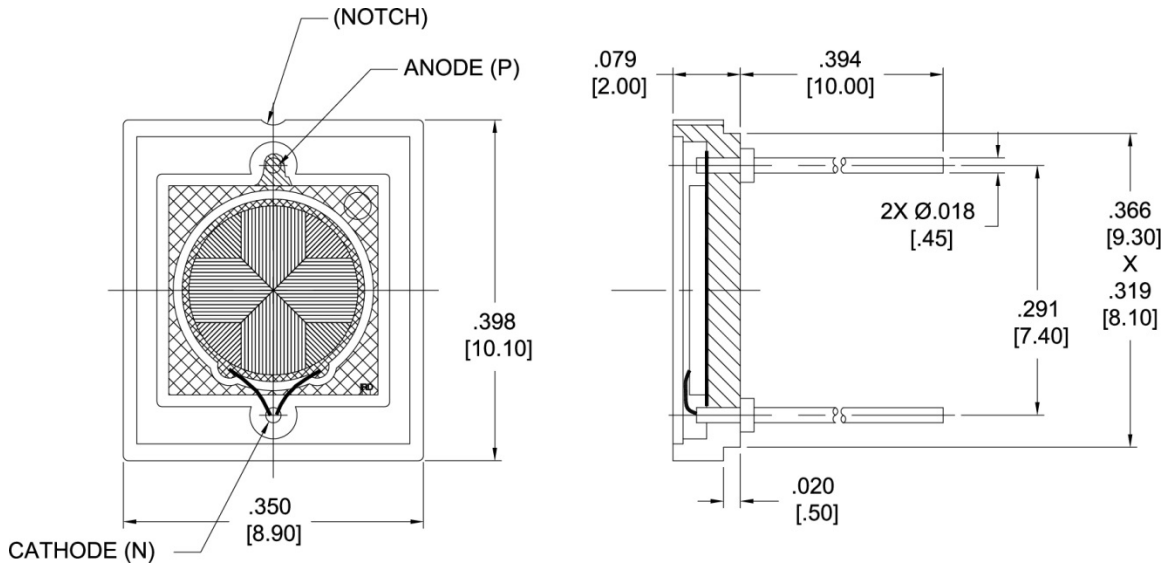
Typical EUV-UV Photon Response



Typical UV-VIS-NIR Photon Responsivity



Package Information



Dimensions are in inch [metric] units.

Ordering Information

ODD-AXU-036	High Speed Circular Photodiode Ideal for Radiation Detection Shipped with Protective Cover

Specifications are subject to change without prior notice.